

# 2SC5954

## Silicon NPN triple diffusion planar type

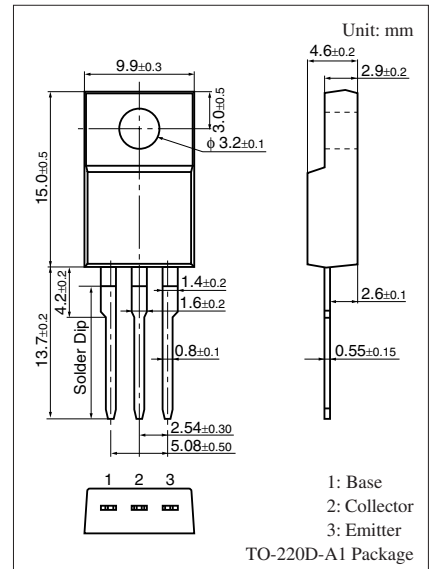
For power amplification with high forward current transfer ratio

### ■ Features

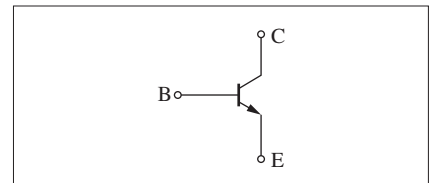
- High forward current transfer ratio  $h_{FE}$  which has satisfactory linearity.
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Full-pack package which can be installed to the heat sink with one screw.

### ■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	80	V
Collector-emitter voltage (Base open)	$V_{CEO}$	60	V
Emitter-base voltage (Collector open)	$V_{EBO}$	6	V
Collector current	$I_C$	3	A
Peak collector current	$I_{CP}$	6	A
Collector power dissipation	$P_C$	25	W
	$T_a = 25^\circ\text{C}$	2.0	
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



### Internal Connection



### ■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 10 \text{ mA}, I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 80 \text{ V}, I_E = 0$			100	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 40 \text{ V}, I_B = 0$			100	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6 \text{ V}, I_C = 0$			100	$\mu\text{A}$
Forward current transfer ratio	$h_{FE1}^*$	$V_{CE} = 4 \text{ V}, I_C = 0.5 \text{ A}$	500		2300	—
	$h_{FE2}$	$V_{CE} = 4 \text{ V}, I_C = 3 \text{ A}$	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1 \text{ A}, I_B = 20 \text{ mA}$			0.6	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_C = 0.1 \text{ A}, f = 10 \text{ MHz}$		200		MHz
Turn-on time	$t_{on}$	$I_C = 1 \text{ A}, \text{Resistance loaded}$		0.2		$\mu\text{s}$
Storage time	$t_{stg}$	$I_{B1} = 0.1 \text{ A}, I_{B2} = -0.1 \text{ A}$		1.5		$\mu\text{s}$
Fall time	$t_f$	$V_{CC} = 50 \text{ V}$		0.1		$\mu\text{s}$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	Q	P
$h_{FE1}$	500 to 1500	1300 to 2300

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